

Substitute for Form 1449 A & B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<i>Complete if Known</i>	
				Application Number	10/564,734
				Confirmation Number	9627
				Filing Date	January 17, 2006
				First Named Inventor	Fumio MATSUMOTO
				Art Unit	Unknown 3432
Examiner Name	H. Fahren				
Attorney Docket Number	Q76643				
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
		US			
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			
F.H. F.H.		JP	1-208396	A	08/22/1989	NIPPON MINING CO.	Abstract
		JP	3-40987	A	02/21/1991	NIPPON TELEGR & TELEPH CORP.	Abstract

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
F.H.		KEIGO HOSHIKAYA, "BULK CRYSTAL GROWING TECHNIQUE", ADVANCED ELECTRONICS SERIES 1-4, PAGES 1-4 and PAGES 236-241	Yes
F.H.		U. SAHR, "GROWTH OF S-DOPED 2" InP-CRYSTALS BY THE VERTICAL GRADIENT FREEZE TECHNIQUE", 2001 INTERNATIONAL CONFERENCE ON INDIUM PHOSPHIDE AND RELATED MATERIALS CONFERENCE PROCEEDINGS, May 14-18, 2001, PAGES 533-536	—

Examiner Signature	<i>Selina F. Fahren</i>	Date Considered	8/17/2006
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JAP6 Rec'd PCT/PTO

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MODIFIED PTO/SB/08 A &amp; B (06-03)

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				Application Number	National Stage of PCT/JP2004/010555
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				Confirmation Number	Unknown
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				Art Unit	Unknown 1722
				Examiner Name	Hiteshew
Sheet	1	of	2	Attorney Docket Number	Q76643

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FH	7	EP	0 971 052	A	01/12/2000	mitsubishi chem. corp.	
FH		EP	0 992 618	A	04/12/2000	JAPAN ENERGY CORP.	

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FH	7	GAULT: "A NOVEL APPLICATION OF THE VERTICAL GRADIENT FREEZE METHOD TO THE GROWTH OF HIGH QUALITY III-V CRYSTALS", JOURNAL OF CRYSTAL GROWTH, NORTH-HOLLAND PUBLISHING CO. AMSTERDAM, NL, Vol. 74, No. 3, 1986, pages 491-506, XP002121188, ISSN: 0022-0248	
FH	7	Y YABUHARA, ET AL, "HIGH QUALITY InP SUBSTRATES GROWN BY THE VCZ METHOD" INDIUM PHOSPHIDE AND RELATED MATERIALS, 1996. IPRM '96., EIGHTH INTERNATIONAL CONFERENCE ON SCHWABISCH-GMUND, GERMANY 21-25 April 1996, NEW YORK, NY, USA, IEEE, US, April 21, 1996, pages 35-38, XP010157617, ISBN: 0-7803-3283-0	
FH	A	YASUMASA OKADA, ET AL, INSTITUTE OF PHYSICS: "DISLOCATION ELIMINATION IN VERTICAL GRADIENT FREEZE GROWN GAAS SINGLE CRYSTALS" GALLIUM ARSENIDE AND RELATED COMPOUNDS., JERSEY, 24-27 SEPT., 1990, PROCEEDINGS OF THE INTERNATIONAL SYMPOSIUM ON GALLIUM ARSENIDE AND RELATED COMPOUNDS. (TITLE FROM 1994 ONWARDS: PROCEEDINGS OF THE INTERNATIONAL SYMPOSIUM ON COMPOUND SEMICONDUCTORS, Vol. SYMP. 17, September 24, 1990, pages 61-66, XP000146745	
FH	7	T. ASAH, ET AL, "VGF CRYSTAL GROWTH AND VAPOR-PHASE FE DOPING TECHNOLOGIES FOR SEMI-INSULATING 100MM DIAMETER INP SUBSTRATES", 1999 11 <sup>TH</sup> INTERNATIONAL CONFERENCE ON INDIUM PHOSPHIDE AND RELATED MATERIALS., CONFERENCE PROCEEDINGS., IPRM DAVOS, MAY 16-20, 1999, INTERNATIONAL CONFERENCE ON INDIUM PHOSPHIDE AND RELATED MATERIALS, NEW YORK, NY: IEEE, US, Vol. Conf. 11, May 16, 1999, pages 249-254, XP000931439, ISBN: 0-7803-5563-6	
FH	Y	YASUMASA OKADA, ET AL, "MECHANISM OF A REDUCTION OF DISLOCATION DENSITIES IN VERTICAL-GRADIENT-FREEZE-GROWN GAAS SINGLE CRYSTALS", JAPANESE JOURNAL OF APPLIED PHYSICS, PUBLICATION OFFICE JAPANESE JOURNAL OF APPLIED PHYSICS., TOKYO, JP, Vol. 29, No. 11 PART 2, November 1, 1990, pages L1954-L1956, XP000232823, ISSN: 0021-4922	

Examiner Signature	<i>[Signature]</i>	Date Considered	8/14/07
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Claims 7-9, 14, 15	FH	PATENT ABSTRACTS OF JAPAN, Vol. 0151, No. 77 (C-0829), May 7, 1991 & JP 3 040987 A (NIPPON TELEGR & TELEPH CORP <NTT>), February 21, 1991	—
Claims 1-6 830-23	FH	D. ZEMKE, ET AL, "GROWTH OF INP BULK CRYSTALS BY VGF: A COMPARATIVE STUDY OF DISLOCATION DENSITY AND NUMERICAL STRESS ANALYSIS", PROCEEDINGS OF THE EIGHTH INTERNATIONAL CONFERENCE ON INDIUM PHOSPHIDE AND RELATED MATERIALS 1996., SCHWABISCH-GMUND, APR. 21-25, 1996, PROCEEDINGS OF THE INTERNATIONAL CONFERENCE ON INDIUM PHOSPHIDE AND RELATED MATERIALS (IPRM), NEW YORK, IEEE, US, Vol. CONF. 8, April 21, 1996, pages 47-49, XP000634431; ISBN: 0-7803-3284-9	—

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